

CHEMICAL SYNTHESIS OF CERAMIC POWDER (PART 3)

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Vapour Phase Reaction

Chemical
Vapour
Deposition
(CVD)

Thermal
Deposition

DC Arc
Plasma



Chemical Vapour Deposition (CVD)


The formation of soot due to incomplete oxidation of firewood is probably the oldest example of deposition using CVD



Chemical Vapour Deposition (CVD)

By definition...

CVD involves the dissociation and/or chemical reactions of gaseous reactants in an activated (heat, light, plasma) environment, followed by the formation of a stable solid product



What is CVD?

Solid material is obtained as a coating, a powder, or as single crystals

Example for Solid-Vapor Reaction

Chemical Vapour Deposition (CVD)

Chemical process used to produce:
high purity
high performance solid materials

Often used in
semiconductor industries
to produce thin film



Types of CVD

CVD's are classified into 2 types on the basis of **operating pressure**.

Atmospheric
Pressure CVD

Low Pressure
CVD

Plasma Enhanced CVD

Thermal CVD

Photochemical Vapour Deposition

Basic Concept

Production of powder particle through:
Homogeneous or heterogeneous nucleation on
supplied **nuclei**.

**Nuclei : point where the crystal start to growth during solidification.*

Reaction typically carried out by passing the
reactants into a chamber (often through a
burner tube with a gas flame).



Basic Concept

Reactants for vapour phase reaction...

Volatiles
gases

Volatiles
liquids

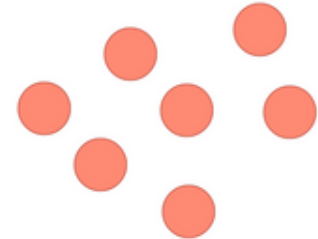
Wide variety of alternative **heat source** such as
plasmas and lasers.



PROCESS



Vapour



Powder

Bulk crystals



Thin film



Whiskers



Substrate



PROCESS



1

Wafer (substrate) exposed to one or more volatile reactants (precursors)

2

Selected reactant materials is diffused in a *carrier gas that flow over the **hot substrate surface**

3

heat from the hot substrate surface prompt chemical reactions between the **reactant** and **carrier gas**

4

volatile **by-products** are also produced- removed by gas flow through the reaction chamber

5

Desired deposit produced

**Carrier gas include O₂, NO₂, CO₂ and H₂.*

Steps involved in CVD

1. Transport of reactants by forced convection to the deposition region

2. Transport of reactants by diffusion from the main gas stream to the substrate surface

3. Adsorption of reactants on the wafer (substrate) surface

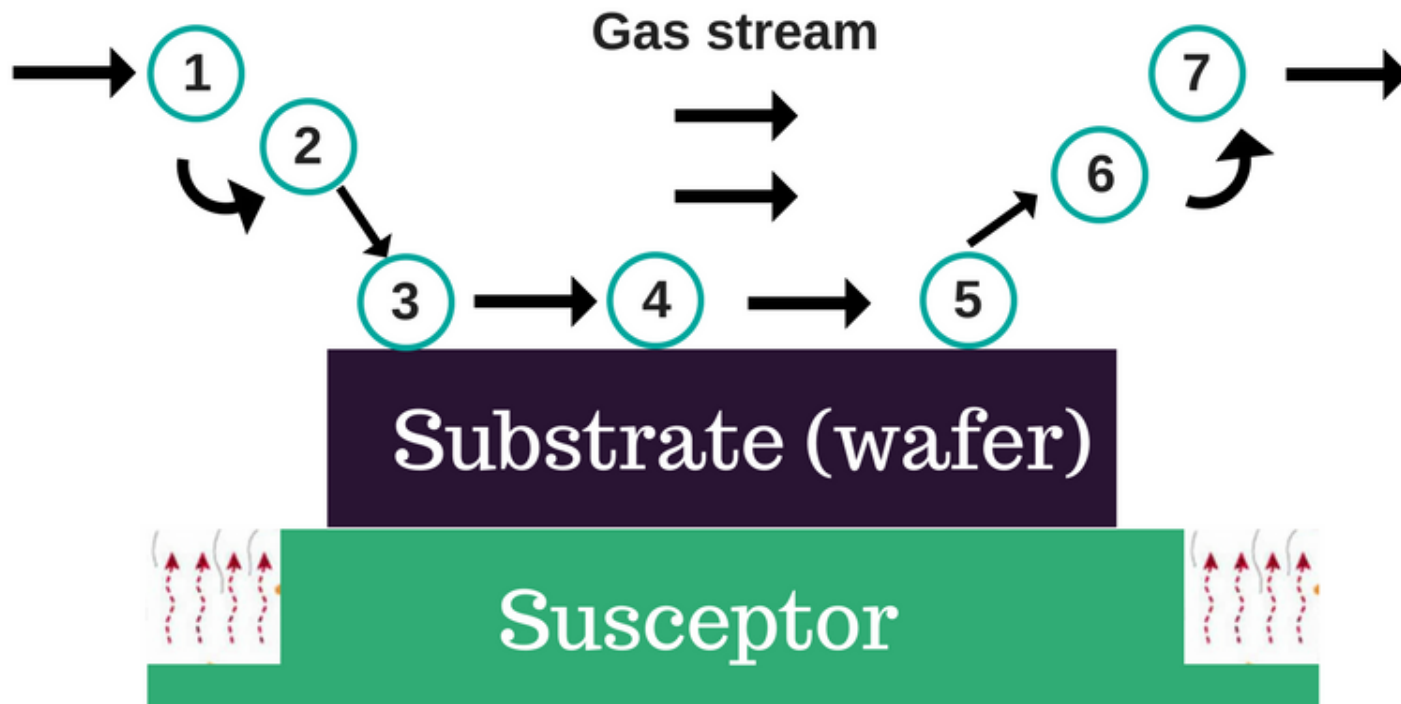
4. Chemical decomposition and other surface reactions take place

7. Transport of by-products by forced convection away from the deposition region

6. Transport of by-products by diffusion

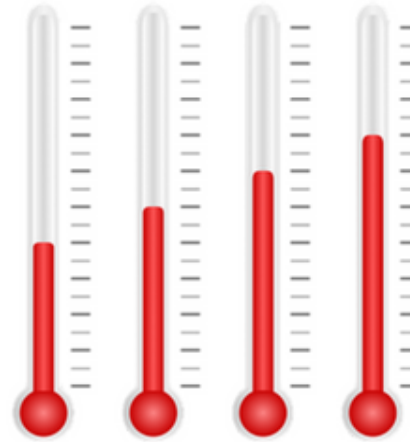
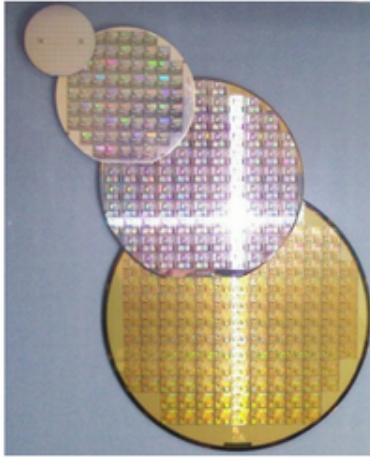
5. Desorption of by-products from the surface

Steps involved in CVD

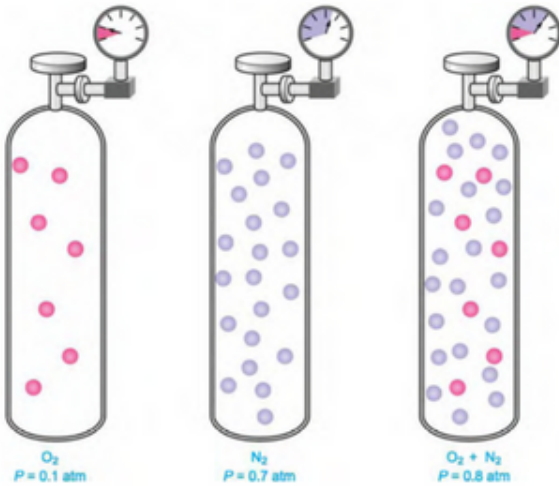


Materials with different properties can be grown by varying the experimental conditions:

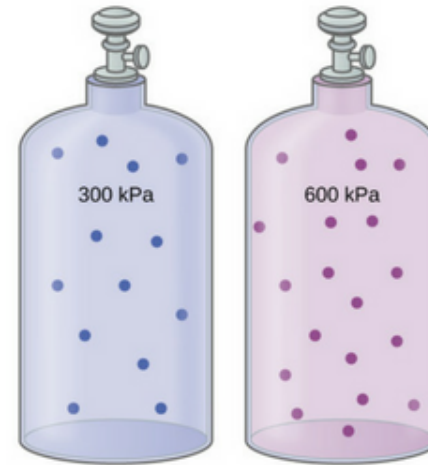
Substrate material



Substrate temperature



composition of the reaction gas mixture



total pressure gas flows

Advantages & Disadvantages of CVD

Versatile – can deposit
any element or compound

High Purity (~99.99%)

High Density – (~100% of theoretical)

Material formation well below T_m

Coating deposited conformal and
near net shape

Economical in production

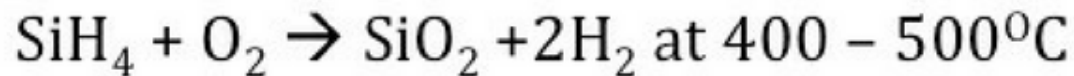


Expensive starting
materials (reactants)

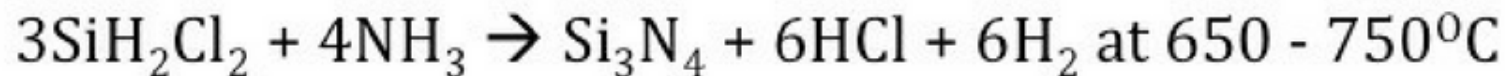
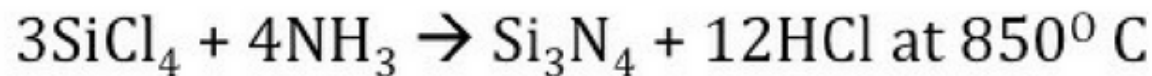
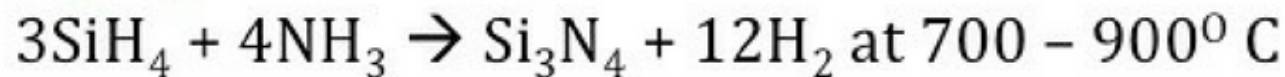
Easily oxidized
(particularly when
producing non oxide
powder)

Chemical reactions of common thin films fabrication by CVD

SiO_2



Si_3N_4





Rate of CVD is affected by:

**Distance in the
direction of gas flow**



Pressure




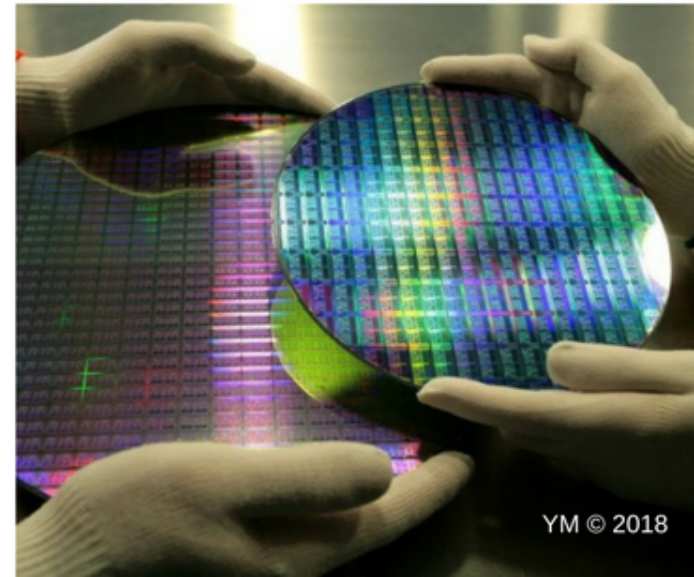
Temperature

**Velocity of carrier
gas**

Better performance can be achieved by either increasing T and gas flow or by reducing pressure and gas velocity

However, increase in T  adverse effect on the substrate due to incompatible CTE of the deposit and substrate

Reducing gas velocity  non-uniformity of the deposition



Applications of CVD



Optical Fibres for telecommunication



Synthetic diamond



Novel powders production

Applications of CVD



Gallium arsenide is used in some photovoltaic devices



Integrated circuits, sensors and optoelectronic devices.



Coatings for wear resistance, corrosion resistance, high temperature protection, erosion protection and combinations thereof